

UNDER DEVELOPMENT

NEW PRODUCT

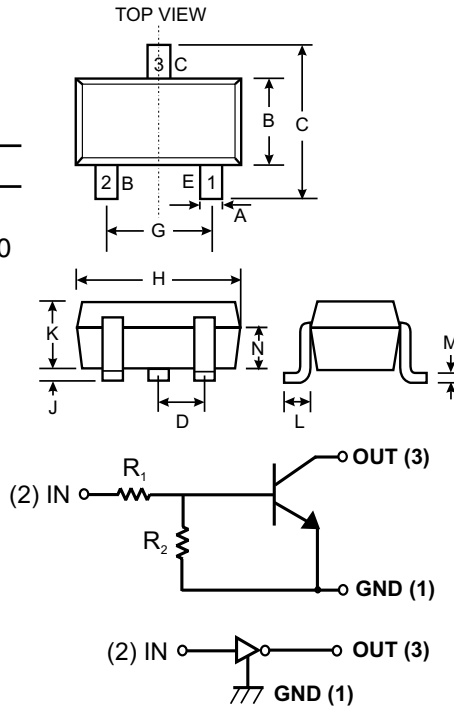
Features

- Epitaxial Planar Die Construction
- Complementary PNP Types Available (DDTA)
- Built-In Biasing Resistors, R1≠R2

Mechanical Data

- Case: SOT-523, Molded Plastic
- Case material - UL Flammability Rating 94V-0
- Terminals: Solderable per MIL-STD-202, Method 208
- Terminal Connections: See Diagram
- Weight: 0.002 grams (approx.)

P/N	R1 (NOM)	R2 (NOM)	MARKING
DDTC113ZE	1K	10K	N02
DDTC123YE	2.2K	10K	N05
DDTC123JE	2.2K	47K	N06
DDTC143XE	4.7K	10K	N09
DDTC143FE	4.7K	22K	N10
DDTC143ZE	4.7K	47K	N11
DDTC114YE	10K	47K	N14
DDTC114WE	10K	4.7K	N15
DDTC124XE	22K	47K	N18
DDTC144VE	47K	10K	N21
DDTC144WE	47K	22K	N22



SOT-523			
Dim	Min	Max	Typ
A	0.15	0.30	0.22
B	0.75	0.85	0.80
C	1.45	1.75	1.60
D	—	—	0.50
G	0.90	1.10	1.00
H	1.50	1.70	1.60
J	0.00	0.10	0.05
K	0.60	0.80	0.75
L	0.10	0.30	0.22
M	0.10	0.20	0.12
N	0.45	0.65	0.50

All Dimensions in mm

SCHEMATIC DIAGRAM

Maximum Ratings @ T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Supply Voltage, (3) to (1)	V _{CC}	50	V
Input Voltage, (2) to (1)	V _{IN}	-5 to +10 -5 to +12 -5 to +12 -7 to +20 -6 to +30 -5 to +30 -6 to +40 -10 to +30 -10 to +40 -15 to +40 -10 to +40	V
Output Current	I _O	100 100 100 100 100 100 70 100 50 30 30	mA
Output Current	I _C (Max)	100	mA
Power Dissipation	P _d	150	mW
Operating and Storage and Temperature Range	T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics @ $T_A = 25^\circ\text{C}$ unless otherwise specified

Characteristic		Symbol	Min	Typ	Max	Unit	Test Condition	
Input Voltage	DDTC113ZE DDTC123YE DDTC123JE DDTC143XE DDTC143FE DDTC143ZE DDTC114YE DDTC114WE DDTC124XE DDTC144VE DDTC144WE	$V_{I(off)}$	0.3 0.3 0.5 0.3 0.3 0.5 0.3 0.8 0.4 1.0 0.8	—	—		V	$V_{CC} = 5V, I_O = 100\mu A$
	DDTC113ZE DDTC123YE DDTC123JE DDTC143XE DDTC143FE DDTC143ZE DDTC114YE DDTC114WE DDTC124XE DDTC144VE DDTC144WE	$V_{I(on)}$	—	—	3.0 3.0 1.1 2.5 1.3 1.3 1.4 3.0 2.5 5.0 4.0		V	$V_O = 0.3V, I_O = 20mA$ $V_O = 0.3V, I_O = 20mA$ $V_O = 0.3V, I_O = 5mA$ $V_O = 0.3V, I_O = 20mA$ $V_O = 0.3V, I_O = 3mA$ $V_O = 0.3V, I_O = 5mA$ $V_O = 0.3V, I_O = 1mA$ $V_O = 0.3V, I_O = 2mA$ $V_O = 0.3V, I_O = 2mA$ $V_O = 0.3V, I_O = 2mA$ $V_O = 0.3V, I_O = 2mA$
Output Voltage		$V_{O(on)}$	—	0.1	0.3	V	$I_O/I_I = 5mA/0.25mA$ DDCT123JE $I_O/I_I = 5mA/0.25mA$ DDCT143ZE $I_O/I_I = 5mA/0.25mA$ DDCT114YE $I_O/I_I = 10mA/0.5mA$ All Others	
Input Current	DDTC113ZE DDTC123YE DDTC123JE DDTC143XE DDTC143FE DDTC143ZE DDTC114YE DDTC114WE DDTC124XE DDTC144VE DDTC144WE	I_I	—	—	7.2 3.8 3.6 1.8 1.8 1.8 0.88 0.88 0.36 0.16 0.16	mA	$V_I = 5V$	
Output Current		$I_{O(off)}$	—	—	0.5	μA	$V_{CC} = 50V, V_I = 0V$	
DC Current Gain	DDTC113ZE DDTC123YE DDTC123JE DDTC143XE DDTC143FE DDTC143ZE DDTC114YE DDTC114WE DDTC124XE DDTC144VE DDTC144WE	G_I	33 33 80 30 68 80 68 24 68 33 56	—	—	—	$V_O = 5V, I_O = 10mA$	
Gain-Bandwidth Product*		f_T	—	250	—	MHz	$V_{CE} = 10V, I_E = 5mA,$ $f = 100MHz$	

* Transistor - For Reference Only

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